

*CLAIM AMENDMENTS*

1. (Currently Amended) A method ~~for~~ of manufacturing a semiconductor device, said method comprising ~~the steps of:~~

forming an insulating film on a semiconductor base material, said insulating film being predominantly composed of organic siloxane and containing an organic component which has no chemical bond to said organic siloxane; and

~~applying plasma treatment to~~ treating said insulating film to remove said organic component and form a modifying layer on a surface of said insulating film.

2. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, ~~wherein including forming said insulating film forming step is performed by a chemical vapor deposition method.~~

3. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, wherein forming said insulating film ~~forming step~~ includes ~~steps of:~~

coating said semiconductor base material with an insulating film composition containing said organic siloxane and said organic component; and

heat treating said insulating film composition at a temperature between 100°C and 200°C.

4. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, ~~wherein said including plasma treatment is performed~~ treating using a gas containing at least one element selected from the group consisting of oxygen, hydrogen, and nitrogen.

5. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, wherein molecules of said organic siloxane contain an alkyl group or an allyl group.

6. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 5, wherein said organic siloxane is ~~MSQ~~ methyl silsesquioxane.

7. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, further comprising ~~a step of~~, after said plasma ~~treatment~~ treating, heat treating said insulating film at a temperature between 250°C and 450°C.

8. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 1, further comprising ~~a step of~~, after said plasma ~~treatment~~ treating, heat treating said insulating film at a temperature between 400°C and 450°C.

9. (Currently Amended) A method ~~for~~ of manufacturing a semiconductor device, said method comprising ~~the steps of~~:

forming an insulating film on a semiconductor base material, said insulating film being composed of organic siloxane; and

~~applying plasma treatment to~~ treating said insulating film to remove an organic group from said organic siloxane and form a modifying layer on a surface of said insulating film.

10. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, ~~wherein~~ including forming said insulating film ~~forming step is performed by a chemical vapor deposition method.~~

11. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, ~~wherein~~ forming said insulating film ~~forming step includes steps of~~:

coating said semiconductor base material with an insulating film composition containing said organic siloxane and said organic component; and

heat treating said insulating film composition at a temperature between 100°C and 200°C.

12. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, wherein said plasma ~~treatment~~ treating is performed using a gas containing at least one element selected from the group consisting of oxygen, hydrogen, and nitrogen.

13. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, wherein molecules of said organic siloxane contain an alkyl group or an allyl group.

14. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 13, wherein said organic siloxane is a phenyl methyl siloxane.

15. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, further comprising ~~a step of~~, after said plasma ~~treatment~~ treating, heat treating said insulating film at a temperature between 250°C and 450°C.

16. (Currently Amended) The method ~~for~~ of manufacturing a semiconductor device according to claim 9, further comprising ~~a step of~~, after said plasma ~~treatment~~ treating, heat treating said insulating film at a temperature between 400°C and 450°C.